



SamHop Microelectronics Corp.

STG8209

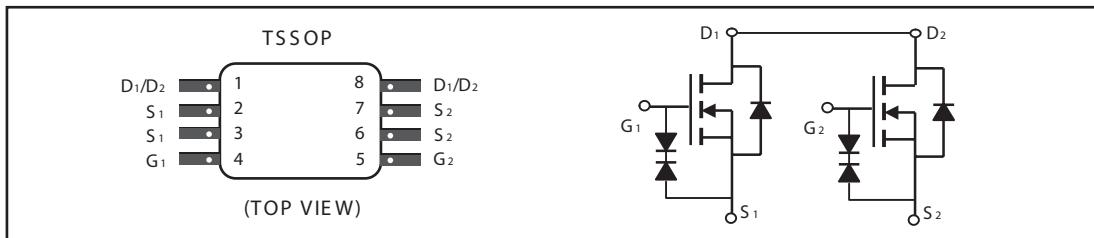
Dec,29.2005

Dual N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
20V	6A	26 @ V _{GS} = 4.0V 40 @ V _{GS} = 2.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous ^a -Pulsed ^b	I _D	6	A
	I _{DM}	24	A
Drain-Source Diode Forward Current ^a	I _S	1.7	A
Maximum Power Dissipation ^a	P _D	1.5	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R _{θJA}	85	°C/W
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STG8209

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			1	μA
Gate-Body Leakage	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 10	μA
ON CHARACTERISTICS^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.8	1.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 4.0V, I_D = 5A$		22	26	m ohm
		$V_{GS} = 2.5V, I_D = 3A$		30	40	m ohm
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 5A$		19		S
DYNAMIC CHARACTERISTICS^c						
Input Capacitance	C_{iss}	$V_{DS} = 8V, V_{GS} = 0V$ $f = 1.0MHz$		693		pF
Output Capacitance	C_{oss}			189		pF
Reverse Transfer Capacitance	C_{rss}			136		pF
SWITCHING CHARACTERISTICS^c						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 10V,$ $I_D = 1A,$ $V_{GEN} = 4.0V,$ $R_{GEN} = 10 \text{ ohm}$		31		ns
Rise Time	t_r			62		ns
Turn-Off Delay Time	$t_{D(OFF)}$			96		ns
Fall Time	t_f			40		ns
Total Gate Charge	Q_g	$V_{DS} = 10V, I_D = 5A,$ $V_{GS} = 4.0V$		11		nC
Gate-Source Charge	Q_{gs}			1.8		nC
Gate-Drain Charge	Q_{gd}			4.9		nC

STG8209

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0 V, I_S = 1.7A$			0.8	1.2

Notes

- a.Surface Mounted on FR4 Board, $t \leq 10\text{sec}$.
- b.Pulse Test Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- c.Guaranteed by design, not subject to production testing.

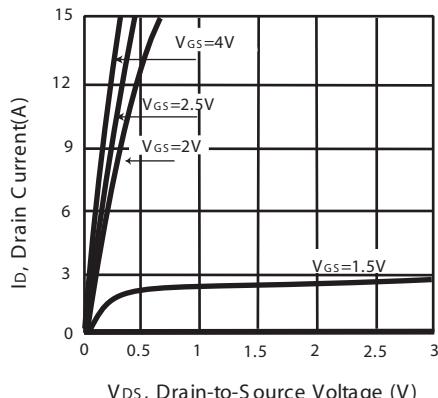


Figure 1. Output Characteristics

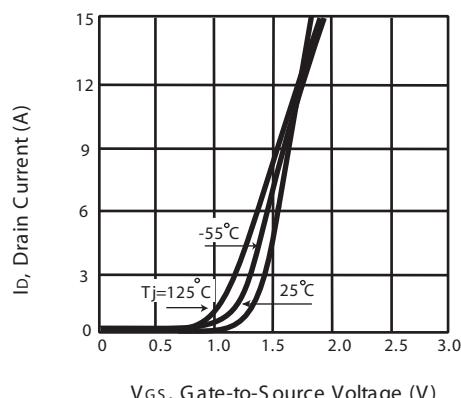


Figure 2. Transfer Characteristics

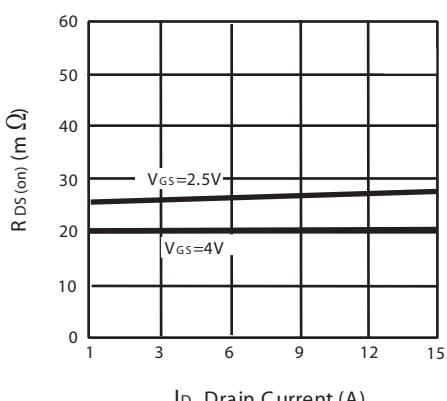


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

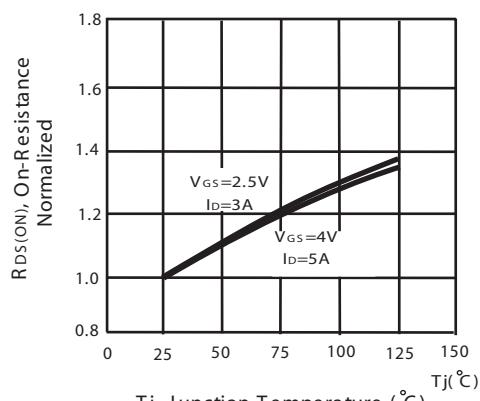


Figure 4. On-Resistance Variation with Drain Current and Temperature

STG8209

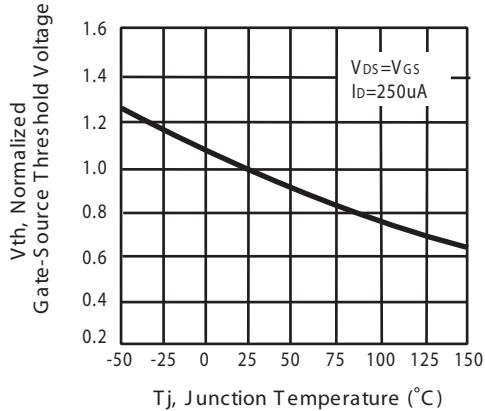


Figure 5. Gate Threshold Variation with Temperature

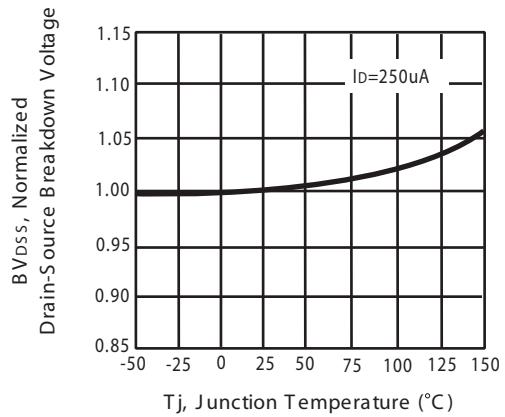


Figure 6. Breakdown Voltage Variation with Temperature

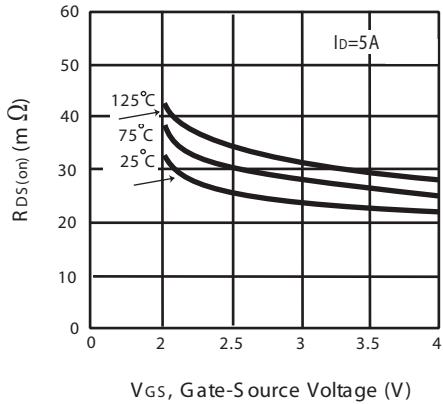


Figure 7. On-Resistance vs. Gate-Source Voltage

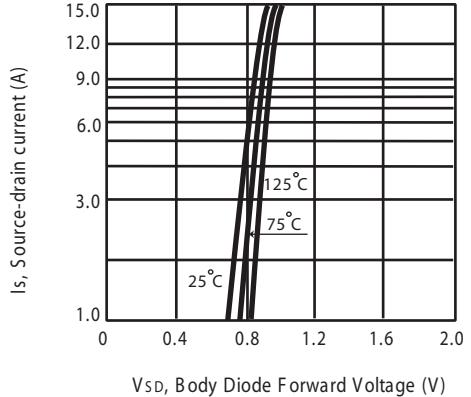


Figure 8. Body Diode Forward Voltage Variation with Source Current

STG8209

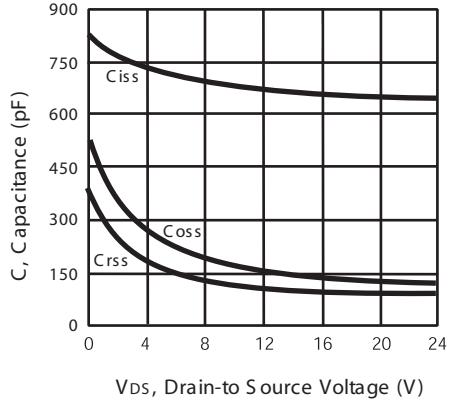


Figure 9. Capacitance

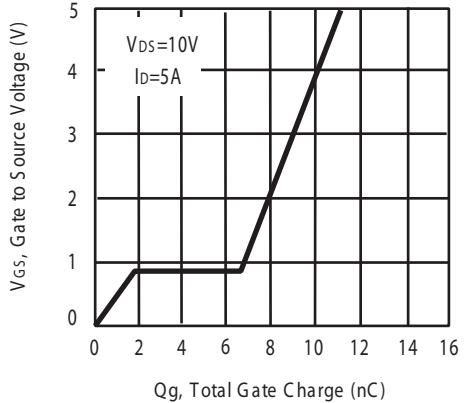


Figure 10. Gate Charge

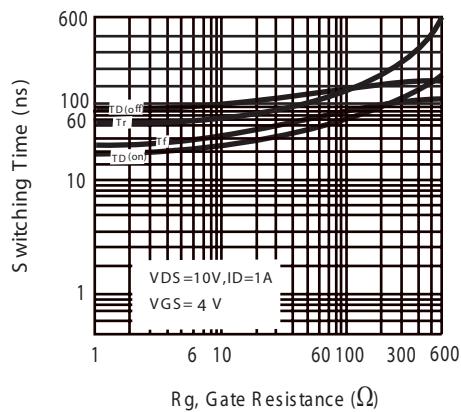


Figure 11. switching characteristics

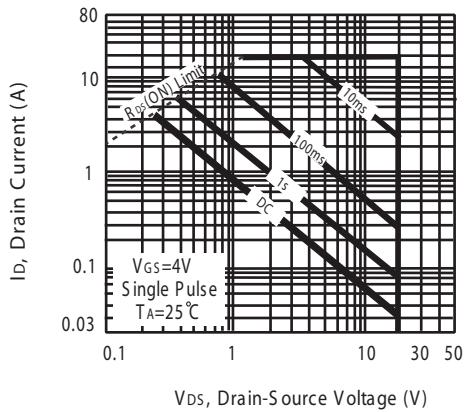


Figure 12. Maximum Safe Operating Area

STG8209

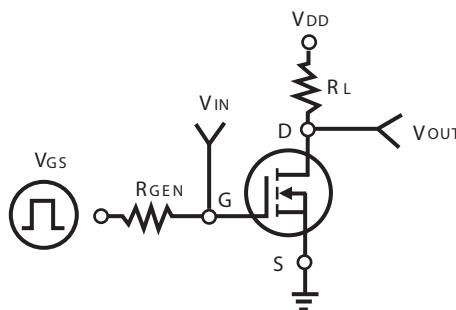


Figure 11. Switching Test Circuit

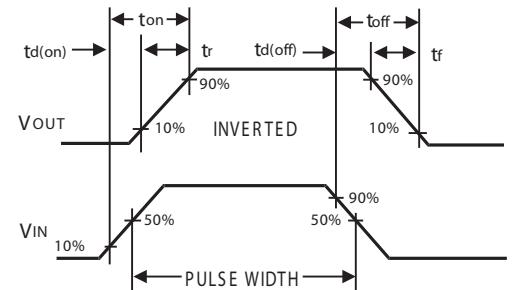
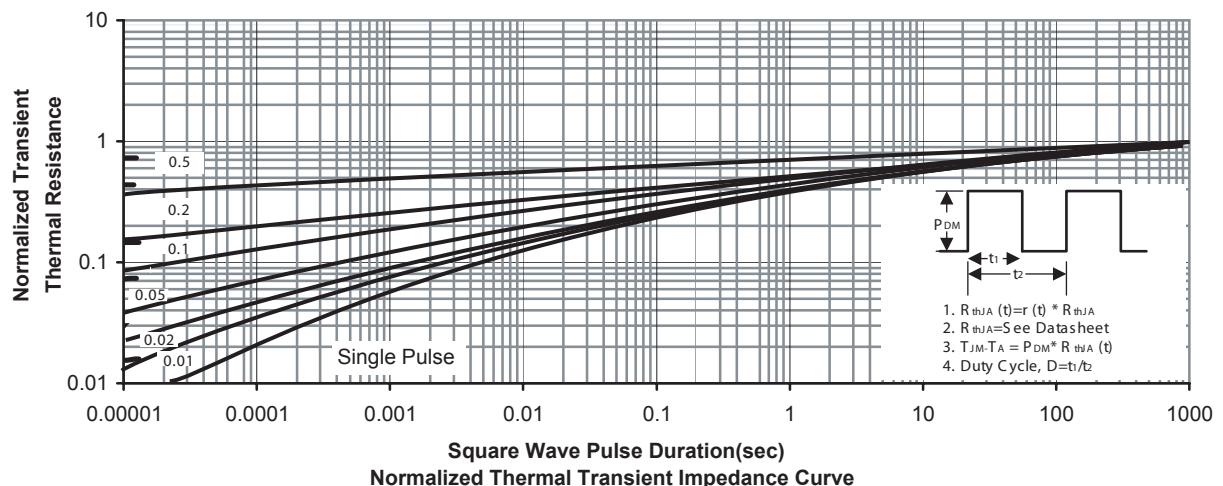


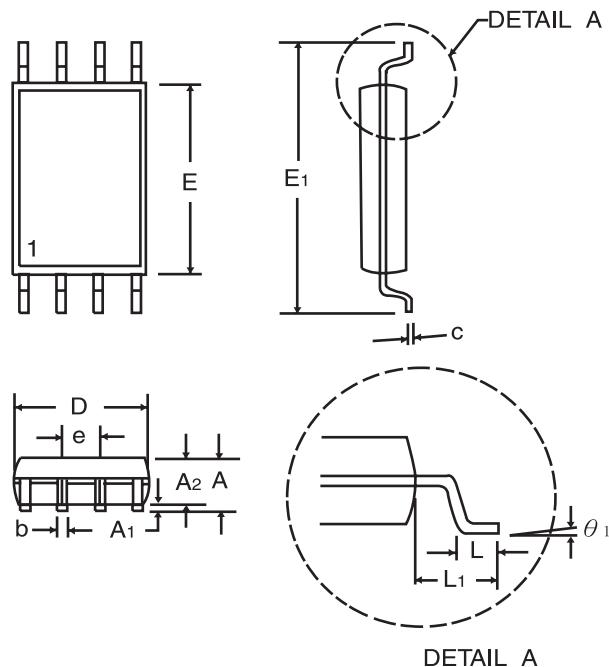
Figure 12. Switching Waveforms



STG8209

PACKAGE OUTLINE DIMENSIONS

TSSOP-8

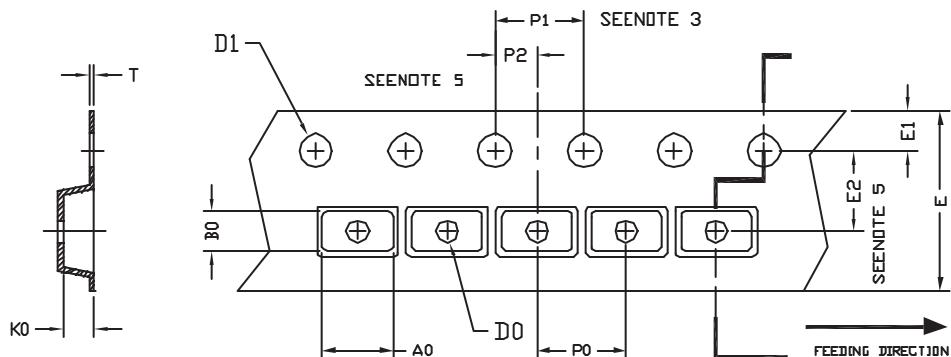


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.05	1.20	0.041	0.047
A1	0.05	0.15	0.002	0.006
A2	-	1.05	-	0.041
b	0.20	0.28	0.008	0.011
c	0.127		0.005	
D-8	2.90	3.10	0.114	0.122
E	4.30	4.50	0.169	0.177
E1	6.20	6.60	0.244	0.260
e	0.65BSC		0.025BSC	
L	0.50	0.70	0.020	0.028
L1	1.00		0.039	
theta_1	0°	8°	0°	8°

STG8209

TSSOP-8 Tape and Reel Data

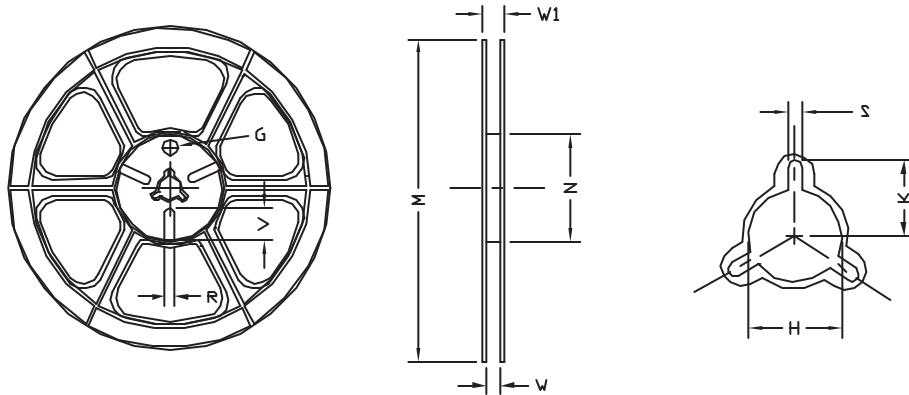
TSSOP-8 Carrier Tape



UNIT : mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TSSOP 8	6.08	4.40	1.60	$\phi 1.50$ + 0.1 - 0.0	$\phi 1.50$ + 0.1 - 0.0	12.00	1.75	5.50 ± 0.05	8.00	4.00	2.00 ± 0.05	0.30 ± 0.05

TSSOP-8 Reel



UNIT : mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330	100	12.5	16.0	$\phi 13.0$ + 0.5 - 0.2	10.6	2.0 ± 0.5	---	---	---